

DCR1020N52

Phase Control Thyristor



DS5964-5 August 2014 (LN31842)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- Medium Voltage Soft Starts
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR1020N52* DCR1020N50	5200 5000	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 100\text{mA}, \\ V_{DRM}, V_{RRM} t_p &= 10\text{ms}, \\ V_{DSM} \& V_{RSM} &= \\ V_{DRM} \& V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. *5000V @ -40°C, 5200V @ 0°C

KEY PARAMETERS

V_{DRM}	5200V
I _{T(AV)}	1018A
I _{TSM}	14800A
dV/dt*	1500V/µs
dI/dt	800A/μs

* Higher dV/dt selections available

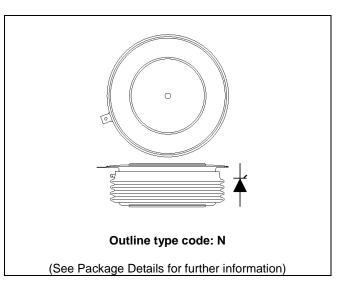


Fig. 1 Package outline

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1020N52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.





CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load	1018	А
I _{T(RMS)}	RMS value	-	1599	А
I _T	Continuous (direct) on-state current	-	1487	А

SURGE RATINGS

Symbol Parameter		Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125$ °C	14.8	kA
I ² t I ² t for fusing		$V_R = 0$	1.097	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.0221	°C/W
		Single side cooled	Anode DC	-	0.041	°C/W
			Cathode DC	-	0.0516	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 23 kN	Double side	-	0.004	°C/W
		(with mounting compound)	Single side	-	0.008	°C/W
T _{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
Fm	Clamping force			20.0	25.0	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	ns	Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	100	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125$ °C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	800	A/µs
		$t_r < 0.5 \mu s, T_j = 125 ^{\circ} C$				
V _{T(TO)}	Threshold voltage – Low level	300A to 750A at T _{case} = 125°	С	-	0.948	V
	Threshold voltage – High level	750A to 4000A at T _{case} = 125°C		-	1.078	V
r _T	On-state slope resistance – Low level	300A to 750A at T _{case} = 125°	С	-	0.783	mΩ
	On-state slope resistance – High level	750A to 4000A at T _{case} = 125°C		-	0.610	mΩ
t _{gd}	Delay time	$V_D = 67\% \ V_{DRM}$, gate source 30V, 10Ω		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	T_j = 125°C,I _{peak} = 1000A, t_p = V_{RM} = 100V, dI/dt = -5A/ μ s,	= 1000us,		1000	μs
		dV _{DR} /dt = 20V/μs linear to 20	V000			
I _{RR}	Reverse recovery current	I_T = 1000A, t_p = 1000us, T_j = 125°C, dI/dt = -5A/ μ s, V_R = 100V		90	115	А
Qs	Stored charge			2200	3800	μC
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	Α
I _H	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500$	0A, I _T = 5A	-	300	mA



GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25°C	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	15	mA

CURVES

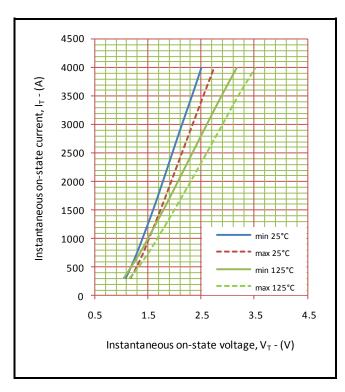


Fig.2 Maximum & minimum on-state characteristics

 V_{TM} EQUATION

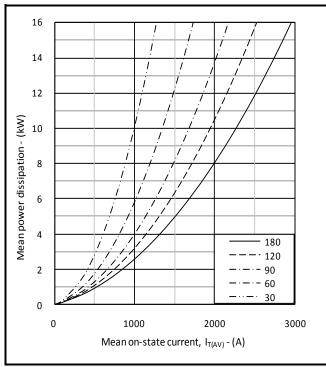
Where A = -0.069834

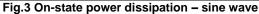
 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$ B = 0.220863 C = 0.000638

C = 0.000638D = -0.013352

these values are valid for $T_j = 125$ °C for $I_T 300$ A to 4000A







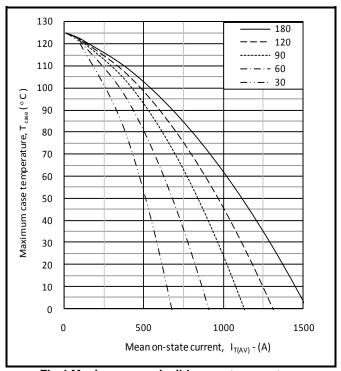


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

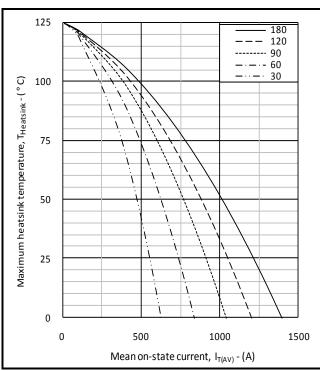


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

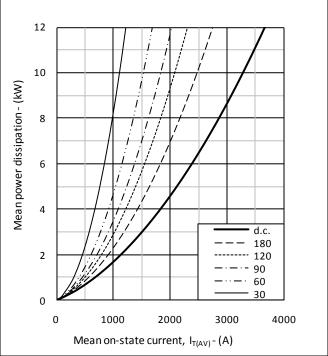


Fig.6 On-state power dissipation - rectangular wave



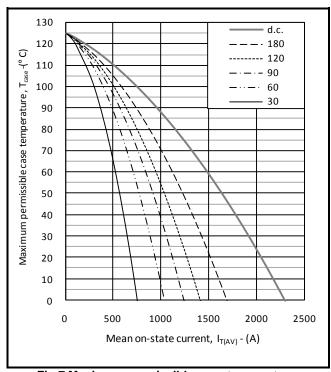


Fig.7 Maximum permissible case temperature, double side cooled - rectangular wave

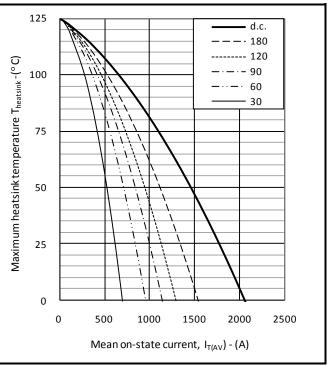
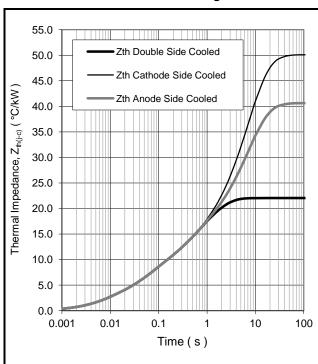


Fig.8 Maximum permissible heatsink temperature, double side cooled - rectangular wave



		1	2	3	4
Double side cooled	R _i (°C/kW)	3.4733	4.9047	9.1463	4.5220
	T _i (s)	0.1457	0.0166	1.2832	0.3767
Anode side cooled	R _i (°C/kW)	7.6674	5.0530	9.7355	27.5992
	T _i (s)	0.2241	0.0169	4.0566	8.2780
Cathode side cooled	R _i (°C/kW)	6.0393	4.2782	5.1301	25.0874
	T _i (s)	0.1356	0.0143	0.6594	7.2358

$$Z_{th} = \sum_{i=1}^{i=4} [R_i \times (1 - \exp(-T/T_i))]$$

$\Delta R_{th(j-c)}$ Conduction

Tables show the increments of thermal resistance $R_{\text{th(j-c)}}$ when the device operates at conduction angles other than d.c.

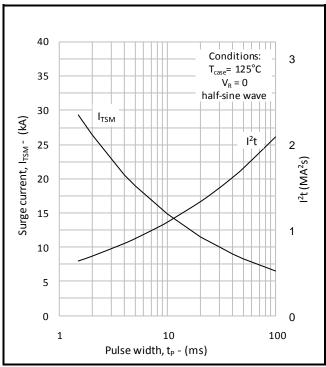
	Double side cooling			Anode Side Cooling			Ca	thode Side	d Cooling
	$\Delta Z_{th}(z)$			ΔZ _{th} (z)				ΔZ_t	_h (z)
θ °	sine.	rect.	θ°	sine.	rect.	T I	θ °	sine.	rect.
180	3.03	2.07	180	3.03	2.07	1 [180	3.12	2.12
120	3.49	2.95	120	3.49	2.95	1 I	120	3.61	3.04
90	3.99	3.43	90	3.99	3.43	1 [90	4.13	3.54
60	4.43	3.94	60	4.43	3.94] [60	4.60	4.08
30	4.77	4.49	30	4.76	4.48	Π	30	4.96	4.66
15	4.92	4.77	15	4.92	4.77] [15	5.13	4.97

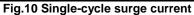
	Alloue Side	Alloue Side Cooling				
	ΔZ_{th} (z)					
θ°	sine.	rect.				
180	3.03	2.07				
120	3.49	2.95				
90	3.99	3.43				
60	4.43	3.94				
30	4.76	4.48				

Callibue Sided Cooling					
	ΔZ _{th} (z)				
θ°	sine.	rect.			
180	3.12	2.12			
120	3.61	3.04			
90	4.13	3.54			
60	4.60	4.08			
30	4.96	4.66			

Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)







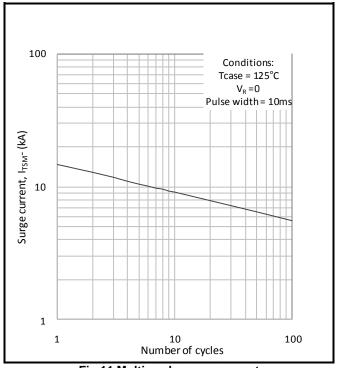


Fig.11 Multi-cycle surge current

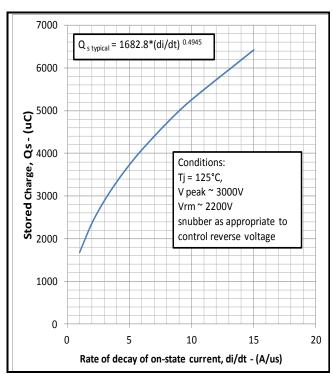


Fig.12 Stored charge

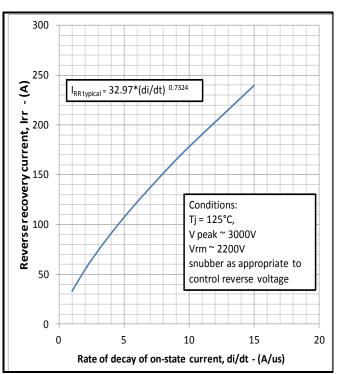


Fig.13 Reverse recovery current

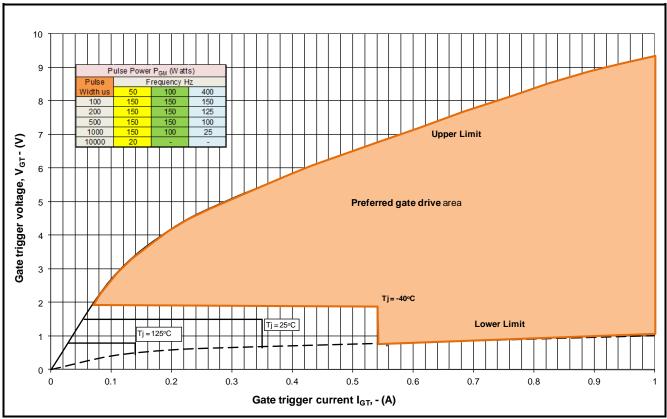


Fig14 Gate Characteristics

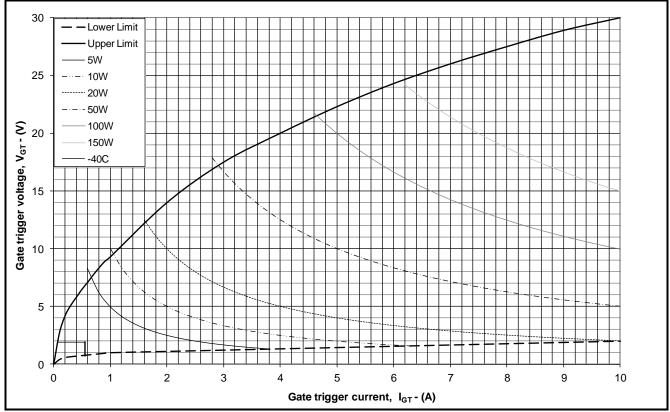


Fig. 15 Gate characteristics





PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

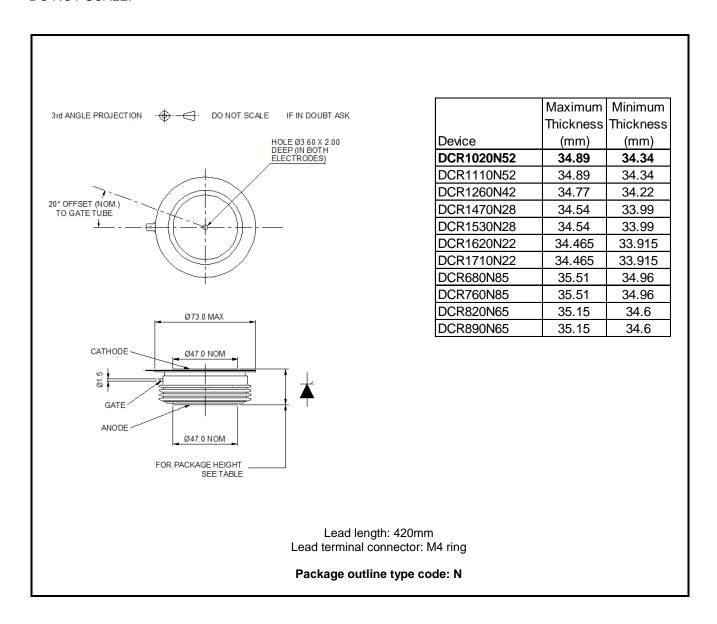


Fig.17 Package outline





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